(Time: 3 Hours) **Total Marks : 80**

N.B.: (1) Question No. 1 is compulsory.

(2)Attempt any three questions out of remaining five.

(3)Figures to the right indicate full marks.

(4)Assume suitable data if required and mention the same in answer sheet.

Q.1 Solve any four **(20)**

a) Draw and explain operation of Depletion type MOSFET.
b) Compare RC coupled,TC coupled and DC coupled amplifier.
c) Explain design consideration of heat sinks in power amplifier.
d) Give the advantages of negative feedback .
e) State and explain Barkhausen's Criteria .

Q.2 (a) Design a two stage RC coupled CE Amplifier to meet following specifications: **(15)**

Av ≥1000,Vo=4V, S=10,f_L=20 Hz.Select BC147B.

. (b) Explain the effect of source and load resistance on amplifier . **(05)**

Q.3 (a) Draw circuit diagram of Class B Push Pull Power amplifier and explain its working. Find its maximum efficiency and maximum power dissipation in each transistor. What is cross-over distortion? How it can be overcome? (**10)**

(b)Draw and explain Cascode amplfier in detail . **(10)**

Q.4 (a)Design a class A transformer coupled power amplifier for the following requirements: Output A.C.power = 5 watts,Load resistance = 12 ohms, DC supply voltage = 12 volts $S_{ICO} \leq 8$.Calculate overall efficiency at full load. **(10)**

(b) Explain the different types of biasing of Depletion MOSFET. **(10)**

Q.5 (a) Explain the different feedback topologies in detail. **(15)**

(b)Write a short notes on Darlington pair amplifier. **(05)**

Q.6 (a) Draw RC phase shift oscillator using BJT and derive the frequency of oscillation for same. **(15)**

(b) For Hartley oscillator calculate the frequency of oscillation if L1=L2= 1 mH and C=0.2 μF. **(05)**

Transistor type	Pdmax @ 25°C Watts	Icmax @ 25°C Amps	$V_{CE}^{(sat)}$ volts d.c.	V_{CBO} volts d.c.	V_{CEO} (Sus) volts d.c.	V_{CER} (Sus) volts d.c.	V_{CEV} volts d.c.	V_{EBO} volts d.c.	T_j max °C	D.C. current gain min	typ.	max.	Small Signal min.	typ.	max.	h_{fe}	V_{BE} max.	θ_{j-c} °C/W	Derate above 25°C W/°C
2N 3055	115·5	15·0	1·1	100	60	70	90	7	200	20	50	70	15	50	120	1·8	1·5	0·7
ECN 055	50·0	5·0	1·0	60	50	55	60	5	200	25	50	100	25	75	125	1·5	3·5	0·4
ECN 149	30·0	4·0	1·0	50	40	—	—	8	150	30	50	110	33	60	115	1·2	4·0	0·3
ECN 100	5·0	0·7	0·6	70	60	65	—	6	200	50	90	280	50	90	280	0·9	35	0·03
BC147A	0·25	0·1	0·25	50	45	50	—	6	125	115	180	220	125	220	260	0·9	—	—
2N 525(PNP)	0·225	0·5	0·25	85	30	—	—	—	100	35	—	65	—	45	—	—	—	—
BC147B	0·25	0·1	0·25	50	45	50	—	6	125	200	290	450	240	330	500	0·9	—	—

Transistor type	hie	hoe	hre	θja
BC 147A	2·7 K Ω	18μ ℧	$1·5 \times 10^{-4}$	0·4°C/mw
2N 525 (PNP)	1·4 K Ω	25μ ℧	$3·2 \times 10^{-4}$	—
BC 147B	4·5 K Ω	30μ ℧	2×10^{-4}	0·4°C/mw
ECN 100	500 Ω	—	—	—
ECN 149	250 Ω	—	—	—
ECN 055	100 Ω	—	—	—
2N 3055	25 Ω	—	—	—

BFW 11—JFET MUTUAL CHARACTERISTICS

−Vgs volts	0·0	0·2	0·4	0·6	0·8	1·0	1·2	1·6	2·0	2·4	2·5	3·0	3·5	4·0
Ids max. mA	10	9·0	8·3	7·6	6·8	6·1	5·4	4·2	3·1	2·2	2·0	1·1	0·5	0·0
Ids typ. mA	7·0	6·0	5·4	4·6	4·0	3·3	2·7	1·7	0·8	0·2	0·0	0·0	0·0	0·0
Ids min. mA	4·0	3·0	2·2	1·6	1·0	0·5	0·0	0·0	0·0	0·0	0·0	0·0	0·0	0·0

N-Channel JFET

Type	V_{os} max. Volts	V_{DG} max. Volts	V_{GS} max. Volts	P_d max. @25°C	T_j max.	I_{DSS}	g_{os} (typical)	$-V_p$ Volts	r_d	Derate above 25°C	θ_{j-a}
2N3822	50	50	50	300 mW	175°C	2 mA	3000 μ ℧	6	50 KΩ	2 mW/°C	0·59°C/mW
BFW 11 (typical)	30	30	30	300 mW	200°C	7 mA	5600 μ ℧	2·5	50 KΩ	—	0·59° C/mW